



**UHBM45**

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI UHBM45** is Designed for

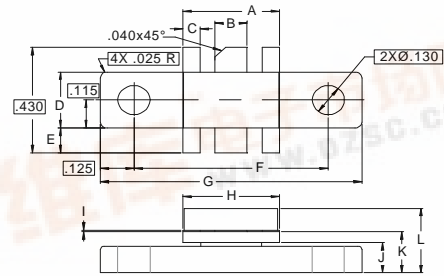
**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	9.0 A
<b>V<sub>CB0</sub></b>	36 V
<b>V<sub>CEO</sub></b>	18 V
<b>V<sub>CES</sub></b>	36 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	150 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.2 °C/W

**PACKAGE STYLE .230 6L FLG**



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

**ORDER CODE: ASI10667**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	36			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 50 mA R <sub>BE</sub> = 10 Ω	18			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			V
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 15 V			5	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V I <sub>C</sub> = 1.0 A	5		200	---
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 12.5 V f = 1.0 MHz		80		pF
<b>P<sub>G</sub></b> <b>η<sub>C</sub></b>	V <sub>CE</sub> = 12.5 V P <sub>OUT</sub> = 45 W f = 836 MHz	4.7	35		dB %

